JCT151C-650R 12A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading
of large current, JCT151C-650R of silicon controlled
rectifiers provides high dV/dt rate with strong
resistance to electromagnetic interference.d [(hi)6 (TcA)t7s 2S,R75.<2 120t i7 (e> iCation 1.11 0

TTw 0U.VL(d)]TJ 2 scnC2_TT0 1 Tf 0 Tc 0 T956 0 9 90.1.92 52.32 T<03C6>.TT3.7d

ORDERING INFORMATION

J	CT	151	C	-650R
JieJie Microelectronics Co., Ltd.	SCRs	$I_{T(RMS)}$:12A	C:TO-220C	650R:V_{DRM} /V_{RRM} ≥ 650V

MARKING

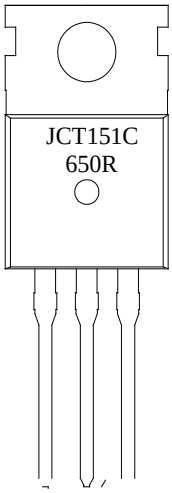
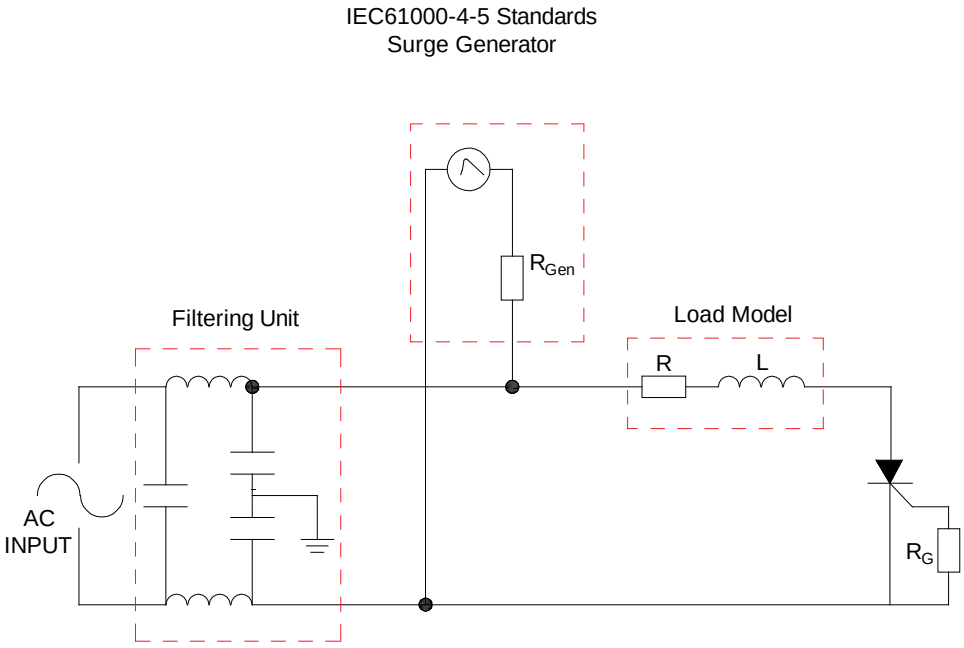


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



PACKAGE MECHANICAL DATA



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.